

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S109	24	(semiconductor with (wafer or substrate)) and (metal bump) and ((sputtering or (ion milling) or (sputter\$3 with etch\$3)) with cleaning)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 20:14
S110	13	S109 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 20:14
S111	833	(semiconductor with (wafer or substrate)) and (metal bump) and ((sputtering or (ion milling) or (sputter\$3 with etch\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 20:32
S112	452	S111 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 20:32
S113	89	S112 and (bump with ((sputtering or (ion milling) or (sputter\$3 with etch\$3))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 20:34
S114	21	S112 and (bump with ((ion milling) or (sputter\$3 with etch\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 20:44
S115	4413	(semiconductor with (wafer or substrate)) and (metal with (bump or ball)) and ((sputtering or (ion milling) or (sputter\$3 with etch\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:01
S116	89	(semiconductor with (wafer or substrate)) and (metal with (bump or ball)) and ((sputtering or (ion milling) or (sputter\$3 with etch\$3)) with cleaning)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:02

S117	64	S116 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 21:02
S118	42	(semiconductor with (wafer or substrate)) and (metal with (bump or ball)) and ((ion milling) and (sputter\$3 with etch \$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:27
S119	15	S118 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 21:28
S120	2	(semiconductor with (wafer or substrate)) and (metal with (bump or ball)) and ((ion milling) with ((AR or argon) and (He or helium)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:35
S121	0	S120 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 21:35
S122	44	(semiconductor with (wafer or substrate)) and (metal with (bump or ball)) and ((ion milling) with ((Ar or argon) or (He or helium)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:36
S123	17	S122 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 21:36
S124	2	(semiconductor with (wafer or substrate)) and (metal with (bump or ball)) and ((ion milling) with (He or helium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:40
S125	2	(semiconductor with (wafer or substrate)) and (bump or ball) and ((ion milling) with (He or helium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:41

S126	13	(semiconductor with (wafer or substrate)) and ((ion milling) with (He or helium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:41
S127	8	S126 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 21:42
S128	10	(semiconductor with (wafer or substrate)) and (metal with (bump or ball)) and ((sputter\$3 with etch\$3) with ((AR or argon) and (He or helium)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:45
S129	6	S128 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 21:45
S130	1	(semiconductor with (wafer or substrate)) and (metal with (bump or ball)) and (((ion milling) and (sputter\$3 with etch \$3)) with cleaning)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:48
S131	42	(semiconductor with (wafer or substrate)) and (metal with (bump or ball)) and ((ion milling) and (sputter\$3 with etch \$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:49
S132	15	S131 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 21:49
S133	431	(semiconductor with (wafer or substrate)) and ((ion milling) with (sputter \$3 with etch\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 21:54
S134	313	S133 and @ad<"20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 21:54

S135	17	("20020011641" "20020180013" "20040040149" "20040043607" "20040088855" "20050046431" "20050064707" "6107109" "6114240" "6294837" "6313434" "6313531" "6429037" "6495448" "6527965" "6773938" "6815709"). PN. OR ("7364985"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/02/07 22:09
S136	57	(semiconductor with (wafer or substrate)) and ((ion milling) with (equivalent or alternative) with (sputter\$3 with etch \$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/02/07 22:13
S137	27	S136 and @ad< "20040225"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/07 22:13

2/ 10/ 2009 12:54:51 PM

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 Contacts\ 10786807 bumps made of gold and its cleaning using ion milling before probing.wsp